

Joseph Woicik

List of Publications by Year in descending order

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101
papers

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citations

136950

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144013

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101
all docs

101
docs citations

101
times ranked

4689
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysing trimethylaluminum infiltration into polymer brushes using a scalable area selective vapor phase process. <i>Materials Advances</i> , 2021, 2, 769-781.	5.4	13
2	Noble-metal dark-edge fermiology: Centrifugal barriers, core-hole memory, and the Zeeman Auger effect. <i>Physical Review B</i> , 2021, 104, .	3.2	0
3	Revealing excitonic processes and chemical bonding in MoS_2 by x-ray spectroscopy. <i>Physical Review B</i> , 2018, 98, .	3.2	11
4	Ferromagnetism and Charge Order from a Frozen Electron Configuration in Strained Epitaxial LaCoO_3 . <i>Physical Review Letters</i> , 2018, 120, 197201.	7.8	26
5	Surface Segregation in Lanthanum Strontium Manganite Thin Films and Its Potential Effect on the Oxygen Reduction Reaction. <i>Journal of the Electrochemical Society</i> , 2017, 164, F3091-F3096.	2.9	7
6	Stability of the M2 phase of vanadium dioxide induced by coherent epitaxial strain. <i>Physical Review B</i> , 2016, 94, .	3.2	62
7	Direct Observation of Electrostatically Driven Band Gap Renormalization in a Degenerate Perovskite Transparent Conducting Oxide. <i>Physical Review Letters</i> , 2016, 116, 027602.	7.8	100
8	Evolution of correlated electron behavior from the surface to the bulk in $\text{Sr}_x\text{Ca}_{1-x}\text{VO}_3$. <i>Materials Research Society Symposia Proceedings</i> , 2015, 1730, 1.	0.1	0
9	Enhanced electron correlations at the $\text{SrTiO}_3/\text{LaTiO}_3$ interface. <i>Physical Review B</i> , 2015, 91, .	3.2	7
10	Loss for photoemission versus gain for Auger: Direct experimental evidence of crystal-field splitting and charge transfer in photoelectron spectroscopy. <i>Physical Review B</i> , 2015, 91, .	3.2	20
11	Evidence of extreme type-III band offset at buried CdO/SnTe interfaces. <i>Physical Review B</i> , 2015, 91, .	3.2	7
12	X-Ray Spectroscopy of Ultra-Thin Oxide/Oxide Heteroepitaxial Films: A Case Study of Single-Nanometer VO_2/TiO_2 . <i>Materials</i> , 2015, 8, 5452-5466.	2.9	23
13	Interfacial Effects in $\mu\text{-LiVOPO}_4$ and Evolution of the Electronic Structure. <i>Chemistry of Materials</i> , 2015, 27, 8211-8219.	6.7	37
14	Effects of rapid thermal annealing on the structural and local atomic properties of ZnO: Ge nanocomposite thin films. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	13
15	The impact of porosity on the formation of manganese based copper diffusion barrier layers on low- ϵ_r dielectric materials. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 325102.	2.8	5
16	Selective Passivation of GeO_2/Ge Interface Defects in Atomic Layer Deposited High- k MOS Structures. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 20499-20506.	8.0	66
17	Electronic structure of C and N co-doped TiO_2 : A combined hard x-ray photoemission spectroscopy and density functional theory study. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	11
18	On the scalability of doped hafnia thin films. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	5

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19	Local structure underlying anomalous tetragonal distortions in BiFeO ₃ -PbTiO ₃ ferroelectrics. Applied Physics Letters, 2014, 104, 242913.	3.3	17
20	Origin of deep subgap states in amorphous indium gallium zinc oxide: Chemically disordered coordination of oxygen. Applied Physics Letters, 2014, 104, .	3.3	67
21	Electron lone pair distortion facilitated metal-insulator transition in In^{2+} -Pb _{0.33} V ₂ O ₅ nanowires. Applied Physics Letters, 2014, 104, .	3.3	15
22	Zr-induced structural changes in Hf _{1-x} Zr _x O ₂ high-k thin films. Applied Physics A: Materials Science and Processing, 2014, 117, 93-96.	2.3	4
23	Nondestructive compositional depth profiling using variable kinetic energy hard X-ray photoelectron spectroscopy and maximum entropy regularization. Surface and Interface Analysis, 2014, 46, 407-417.	1.8	10
24	Nature of the Metal Insulator Transition in Ultrathin Epitaxial Vanadium Dioxide. Nano Letters, 2013, 13, 4857-4861.	9.1	90
25	La-doped BaSnO ₃ "Degenerate perovskite transparent conducting oxide: Evidence from synchrotron x-ray spectroscopy. Applied Physics Letters, 2013, 103, .	3.3	81
26	Origin of the Bipolar Doping Behavior of SnO from X-ray Spectroscopy and Density Functional Theory. Chemistry of Materials, 2013, 25, 3114-3123.	6.7	135
27	Band alignment in Ge/GeO _x /HfO ₂ /TiO ₂ heterojunctions as measured by hard x-ray photoelectron spectroscopy. Applied Physics Letters, 2012, 101, .	3.3	10
28	Structure of SrTiO_3 Films on Si. Physical Review Letters, 2012, 108, 166101.	7.8	24
29	Local atomic and electronic structures of epitaxial strained LaCoO ₃ thin films. Physical Review B, 2012, 85, .	3.2	54
30	Atomistic calculation of the local structure in bulk and strained semiconductor alloys. Journal of Applied Physics, 2012, 112, .	2.5	4
31	Composition dependent bilayer atomic ordering in Al _x Ga _{1-x} N films examined by polarization-dependent extended x-ray absorption fine structure. Applied Physics Letters, 2012, 100, .	3.3	22
32	Annealing dependence of diamond-metal Schottky barrier heights probed by hard x-ray photoelectron spectroscopy. Applied Physics Letters, 2012, 100, .	3.3	22
33	Crystal structure and powder diffraction reference pattern of type I clathrate Ba ₈ Ni ₄ Ge ₄₂ . Powder Diffraction, 2012, 27, 25-31.	0.2	2
34	Boron migration due to annealing in CoFeB/MgO/CoFeB interfaces: A combined hard x-ray photoelectron spectroscopy and x-ray absorption studies. Applied Physics Letters, 2011, 99, 222502.	3.3	18
35	Performance of a four-element Si drift detector for X-ray absorption fine-structure spectroscopy: resolution, maximum count rate, and dead-time correction with incorporation into the ATHENA data analysis software. Journal of Synchrotron Radiation, 2010, 17, 409-413.	2.4	36
36	Effects of annealing on the local structure of Fe and Co in CoFeB/MgO/CoFeB tunnel junctions: An extended x-ray-absorption fine structure study. Applied Physics Letters, 2010, 96, .	3.3	30

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37	Temperature-dependent local structure of LaFeAsO $1-x$ F x : Probing the atomic correlations. Journal of Applied Physics, 2010, 108, 123715.	2.5	12
38	Band alignment of atomic layer deposited HfO 2 on clean and N passivated germanium surfaces. Applied Physics Letters, 2010, 97, .	3.3	16
39	Displacive Ordering Transitions in Perovskite-Like AgNb $_{1/2}$ Ta $_{1/2}$ O $_3$. Chemistry of Materials, 2010, 22, 4987-4995.	6.7	63
40	A combined fit of total scattering and extended X-ray absorption fine structure data for local-structure determination in crystalline materials. Journal of Applied Crystallography, 2009, 42, 867-877.	4.5	51
41	Oxygen vacancies in N doped anatase TiO 2 : Experiment and first-principles calculations. Applied Physics Letters, 2009, 95, .	3.3	140
42	A Ferroelectric Oxide Made Directly on Silicon. Science, 2009, 324, 367-370.	12.6	347
43	Strain-induced change in local structure and its effect on the ferromagnetic properties of La $_{0.5}$ Sr $_{0.5}$ CoO $_3$ thin films. Applied Physics Letters, 2008, 93, 182507.	3.3	42
44	Domain ordering of strained 5 ML SrTiO $_3$ films on Si(001). Applied Physics Letters, 2007, 90, 221908.	3.3	5
45	Separation of the strain and finite size effect on the ferromagnetic properties of La $_{0.5}$ Sr $_{0.5}$ CoO $_3$ thin films. Applied Physics Letters, 2007, 91, 172509.	3.3	28
46	Synchrotron X-ray Based Characterization of CdZnTe Crystals. Journal of Electronic Materials, 2007, 36, 1092-1097.	2.2	9
47	Imaging defects in strained-silicon thin films by glancing-incidence x-ray topography. Applied Physics Letters, 2006, 88, 224102.	3.3	5
48	Direct Measurement of Valence-Charge Asymmetry by X-Ray Standing Waves. Physical Review Letters, 2000, 84, 773-776.	7.8	23
49	X-Ray Anomalous Scattering Study of a Charge-Ordered State in NaV $_2$ O $_5$. Physical Review Letters, 2000, 85, 4349-4352.	7.8	73
50	Layer perfection in ultrathin InAs quantum wells in GaAs(001). Physical Review B, 2000, 61, 2073-2084.	3.2	16
51	Extended x-ray absorption fine-structure measurement of bond-length strain in epitaxial Gd $_2$ O $_3$ on GaAs(001). Applied Physics Letters, 2000, 76, 2526-2528.	3.3	11
52	Lattice compression of Si crystals and crystallographic position of As impurities measured with x-ray standing wave spectroscopy. Journal of Applied Physics, 1999, 85, 1429-1437.	2.5	15
53	Atomic-resolution study of lattice distortions of buried In $_x$ Ga $_{1-x}$ As monolayers in GaAs(001). Physical Review B, 1999, 60, 13612-13618.	3.2	12
54	Bond lengths in semiconductor alloys. Journal of Synchrotron Radiation, 1999, 6, 570-572.	2.4	1

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55	Layer perfection in ultrathin MOVPE-grown InAs layers buried in GaAs(001) studied by X-ray standing waves and photoluminescence spectroscopy. <i>Journal of Synchrotron Radiation</i> , 1999, 6, 500-502.	2.4	27
56	Reliability of structural parameters determined from DAFS data using the iterative dispersion integral algorithm. <i>Journal of Synchrotron Radiation</i> , 1999, 6, 335-337.	2.4	9
57	Bond-length strain in buried Ga _{1-x} In _x As thin-alloy films grown coherently on InP(001). <i>Applied Physics Letters</i> , 1998, 73, 1269-1271.	3.3	22
58	Random-cluster calculation of bond lengths in strained-semiconductor alloys. <i>Physical Review B</i> , 1998, 57, 6266-6269.	3.2	32
59	Diffraction anomalous fine-structure study of strained Ga _{1-x} In _x As on GaAs(001). <i>Physical Review B</i> , 1998, 58, R4215-R4218.	3.2	26
60	Phase-correct bond lengths in crystalline Ge _x Si _{1-x} alloys. <i>Physical Review B</i> , 1998, 57, 14592-14595.	3.2	26
61	Cr K edge x-ray absorption study of Cr dopants in Mg ₂ SiO ₄ and Ca ₂ GeO ₄ . <i>Applied Physics Letters</i> , 1997, 71, 1168-1170.	3.3	20
62	Bond-Length Distortions in Strained Semiconductor Alloys. <i>Physical Review Letters</i> , 1997, 79, 5026-5029.	7.8	69
63	Unit cell of strained GeSi. <i>Physical Review B</i> , 1997, 55, 15386-15389.	3.2	32
64	Extended x-ray absorption fine structure study of Al _x Ga _(1-x) N films. <i>Applied Physics Letters</i> , 1997, 70, 2108-2110.	3.3	49
65	Preferential site distribution of dilute Pt and Ta in CoCr-based films: An extended x-ray absorption fine structure study. <i>Journal of Applied Physics</i> , 1997, 82, 2912-2917.	2.5	6
66	Surface structure of cadmium selenide nanocrystallites. <i>Physical Review B</i> , 1997, 55, 13822-13828.	3.2	70
67	Surface-sensitive x-ray standing-wave study of Si(111)3 $\sqrt{3}$ -Ag. <i>Physical Review B</i> , 1996, 53, 15425-15428.	3.2	9
68	Strain and relaxation in InAs and InGaAs films grown on GaAs(001). <i>Applied Physics Letters</i> , 1996, 68, 3010-3012.	3.3	23
69	Evolution of the crystallographic position of As impurities in heavily doped Si crystals as their electrical activity changes. <i>Applied Physics Letters</i> , 1996, 68, 3090-3092.	3.3	23
70	The role of Ta and Pt in segregation within Co-Cr-Ta and Co-Cr-Pt thin film magnetic recording media. <i>Journal of Applied Physics</i> , 1996, 79, 5345.	2.5	8
71	Near-neighbor mixing and bond dilation in mechanically alloyed Cu-Fe. <i>Physical Review B</i> , 1996, 54, 6929-6940.	3.2	124
72	Order-to-disorder phase-transition study of Pb on Ge(111). <i>Physical Review B</i> , 1995, 51, 2440-2445.	3.2	19

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73	Attenuation of photons at 14-keV energies in helium. <i>Physical Review A</i> , 1995, 51, 447-453.	2.5	10
74	High-resolution structural study of Bi on Si(001). <i>Physical Review B</i> , 1995, 52, R5515-R5518.	3.2	27
75	Large-angle bond-rotation relaxation for CdTe(110). <i>Physical Review B</i> , 1995, 51, 10774-10778.	3.2	13
76	Accommodation of strain in ultrathin InAs/GaAs films. <i>Physical Review B</i> , 1995, 52, R2281-R2284.	3.2	54
77	Design and performance of the Advanced Light Source double-crystal monochromator. <i>Review of Scientific Instruments</i> , 1995, 66, 1748-1750.	1.3	15
78	Structural determination of the Si(111)-Bi surface by x-ray standing waves and scanning tunneling microscopy. <i>Physical Review B</i> , 1994, 50, 12246-12249.	3.2	18
79	Surface extended x-ray-absorption fine-structure study of the (1 monolayer Sb)/GaP(110) interface. <i>Physical Review B</i> , 1993, 47, 6444-6449.	3.2	11
80	In/Si(111)- interface: An unrelaxed T ₄ geometry. <i>Physical Review Letters</i> , 1993, 71, 1204-1207.	7.8	34
81	Band-structure effects in the excitation-energy dependence of Si _{2,3} x-ray-emission spectra. <i>Physical Review B</i> , 1993, 48, 1918-1920.	3.2	54
82	Diffraction anomalous fine structure: A new x-ray structural technique. <i>Physical Review Letters</i> , 1992, 69, 3064-3067.	7.8	217
83	Extended x-ray-absorption fine-structure determination of bond-length conservation at the clean InP(110) surface. <i>Physical Review B</i> , 1992, 46, 9869-9872.	3.2	11
84	X-ray standing-wave determination of the clean InP(110) surface reconstruction. <i>Physical Review Letters</i> , 1992, 68, 341-344.	7.8	45
85	X-ray, soft x-ray, and VUV beam position monitor. <i>Review of Scientific Instruments</i> , 1992, 63, 526-529.	1.3	8
86	Gold-induced germanium crystallization. <i>Physical Review B</i> , 1992, 46, 9505-9510.	3.2	72
87	Silicide formation and structural evolution in Fe-, Co-, and Ni-implanted silicon. <i>Physical Review B</i> , 1992, 46, 4077-4085.	3.2	29
88	Structural characterization of the (1 monolayer Sb)/GaP(110) interface using x-ray standing waves. <i>Physical Review B</i> , 1992, 46, 6869-6874.	3.2	18
89	X-ray standing-wave study of monolayers of Sb on GaAs(110). <i>Physical Review B</i> , 1992, 46, 7276-7279.	3.2	31
90	In situ XANES of an iron porphyrin irreversibly adsorbed on an electrode surface. <i>Journal of the American Chemical Society</i> , 1991, 113, 9063-9066.	13.7	38

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91	Local bonding structure of Sb on Si(111) by surface extended x-ray-absorption fine structure and photoemission. Physical Review B, 1991, 43, 4331-4339.	3.2	27
92	Conservation of bond lengths in strained Ge-Si layers. Physical Review B, 1991, 43, 2419-2422.	3.2	59
93	Determination of the Sb/Si(111) interfacial structure by back-reflection x-ray standing waves and surface extended x-ray-absorption fine structure. Physical Review B, 1991, 44, 3475-3478.	3.2	30
94	Semiconductor surface core level shifts by use of selected overlayers. Physica Scripta, 1990, 41, 1034-1036.	2.5	4
95	Surface extended-x-ray-absorption fine structure and scanning tunneling microscopy of Si(001)2Å-1-Sb. Physical Review Letters, 1990, 65, 3417-3420.	7.8	141
96	Morphology and barrier-height development of Bi/InP(110) interfaces. Physical Review B, 1990, 42, 3017-3023.	3.2	13
97	Strontium-induced oxygen defect structure and hole doping in La _{2-x} Sr _x CuO ₄ . Physical Review Letters, 1990, 64, 2715-2718.	7.8	55
98	Polarization x-ray-absorption near-edge structure study of Pr _{2-x} Ce _x CuO ₄ single crystals: The nature of Ce doping. Physical Review B, 1990, 42, 1037-1040.	3.2	24
99	Si(111) 2Å-1 surface core-level shifts investigated by use of Ge overlayer. Physical Review B, 1989, 40, 12463-12467.	3.2	16
100	Silicon (111) 2Å-1 surface states: K-edge transitions and surface-selective L _{2,3} VV Auger line shape. Physical Review B, 1989, 39, 8593-8604.	3.2	24
101	Photon-energy-sensitive Si L _{2,3} VV Auger satellite. Physical Review B, 1989, 39, 6048-6051.	3.2	8